

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized applications, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an equif prese



November 2013

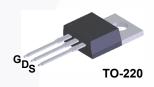
FQP32N20C / FQPF32N20C N-Channel QFET[®] MOSFET 200 V, 28 A, 82 mΩ

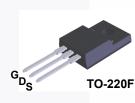
Features

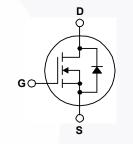
- 28 A, 200 V, ${\sf R}_{{\sf DS}({\sf on})}$ = 82 m Ω (Max.) @ ${\sf V}_{{\sf GS}}$ = 10 V, ${\sf I}_{{\sf D}}$ = 14 A
- Low Gate Charge (Typ. 82.5 nC)
- Low Crss (Typ. 185 pF)
- 100% Avalanche Tested

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.







MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Parameter			FQP32N20C	FQPF32N20C	Unit
Drain to Source Voltage			200		V
Drain Current	-Continuous (T _C = 25 ^o C)	-Continuous (T _C = 25 ^o C) -Continuous (T _C = 100 ^o C)		28.0 *	А
Drain Current	-Continuous (T _C = 100 ^o C)			17.8 *	А
Drain Current	- Pulsed	(Note 1)	112	112 *	А
Gate to Source Voltage			± 30		V
Single Pulsed Avalanche Energy		(Note 2)	955		mJ
Avalanche Current		(Note 1)	28.0		А
Repetitive Avalanche Energy		(Note 1)	15.6		mJ
Peak Diode Recovery dv/dt		(Note 3)	5.5		V/ns
Dower Dissinction	(T _C = 25°C)		156	50	W
Power Dissipation	- Derate above 25°C		1.25	0.4	W/°C
Operating and Storage Temperature Range		-55 to +150		°C	
Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300		°C
	Drain Current Drain Current Gate to Source Voltage Single Pulsed Avalanch Avalanche Current Repetitive Avalanche E Peak Diode Recovery c Power Dissipation Operating and Storage Maximum Lead Temper	$\begin{tabular}{ c c c c } \hline Drain to Source Voltage & -Continuous (T_C = 25^\circ C) & -Continuous (T_C = 100^\circ C) \\ \hline Drain Current & -Pulsed \\ \hline Drain Current & -Pulsed \\ \hline Gate to Source Voltage & Single Pulsed Avalanche Energy & Avalanche Current \\ \hline Repetitive Avalanche Energy & Peak Diode Recovery dv/dt & Power Dissipation & (T_C = 25^\circ C) & -Derate above 25^\circ C \\ \hline Operating and Storage Temperature Range & Maximum Lead Temperature for Soldering Purpose, \\ \hline \end{tabular}$	$\begin{tabular}{ c c c c } \hline Drain to Source Voltage & -Continuous (T_C = 25^{\circ}C) & -Continuous (T_C = 100^{\circ}C) & -Pulsed & (Note 1) & -Pulsed & (Note 2) & -Pulsed & (Note 2) & -Pulsed & -Avalanche Energy & (Note 2) & -Avalanche Current & (Note 1) & -Avalanche Current & (Note 1) & -Peak Diode Recovery dv/dt & (Note 3) & -Peak Diode Recovery dv/dt & (Note 3) & -Peak Diode Recovery dv/dt & (Note 3) & -Peate above 25^{\circ}C & -Perate above 25^{\circ}C $	Drain to Source Voltage24Drain Current-Continuous ($T_C = 25^{\circ}C$) -Continuous ($T_C = 100^{\circ}C$)28.0Drain Current-Pulsed(Note 1)Drain Current-Pulsed(Note 1)Gate to Source Voltage±Single Pulsed Avalanche Energy(Note 2)Avalanche Current(Note 1)Repetitive Avalanche Energy(Note 1)Peak Diode Recovery dv/dt(Note 3)Power Dissipation($T_C = 25^{\circ}C$) - Derate above $25^{\circ}C$ 156Operating and Storage Temperature Range-55 toMaximum Lead Temperature for Soldering Purpose,30	Drain to Source Voltage200Drain Current-Continuous ($T_C = 25^{\circ}C$) -Continuous ($T_C = 100^{\circ}C$)28.0Drain Current-Pulsed(Note 1)Drain Current-Pulsed(Note 1)Gate to Source Voltage ± 30 Single Pulsed Avalanche Energy(Note 2)Avalanche Current(Note 1)Repetitive Avalanche Energy(Note 1)Repetitive Avalanche Energy(Note 1)Peak Diode Recovery dv/dt(Note 3) $C_C = 25^{\circ}C$) - Derate above $25^{\circ}C$ 156Power Dissipation $(T_C = 25^{\circ}C)$ - Derate above $25^{\circ}C$ Operating and Storage Temperature Range-55 to +150Maximum Lead Temperature for Soldering Purpose,300

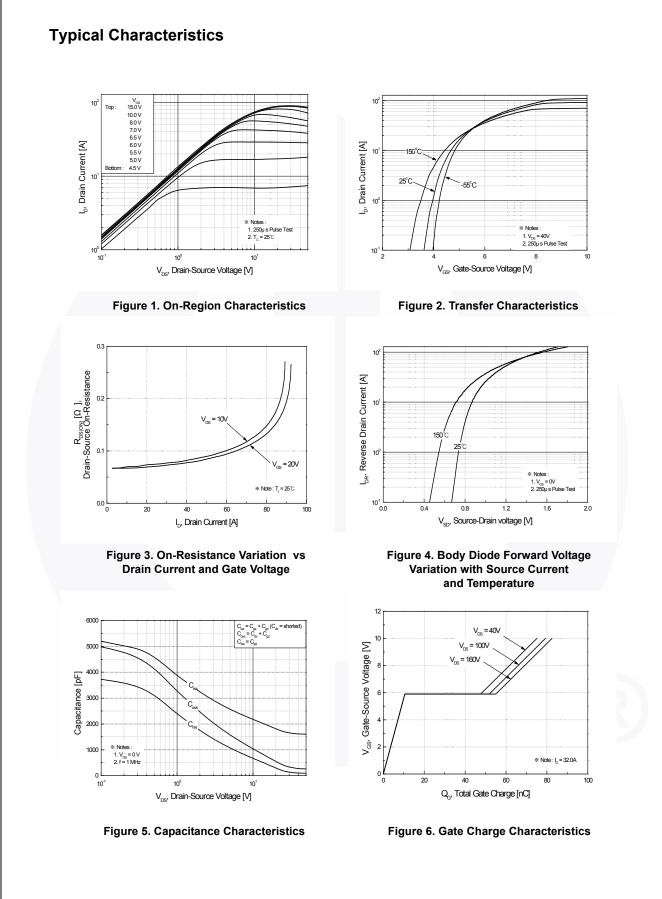
Thermal Characteristics

Symbol	Parameter	FQP32N20C	FQPF32N20C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.8	2.51	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max	62.5	62.5	°C/W

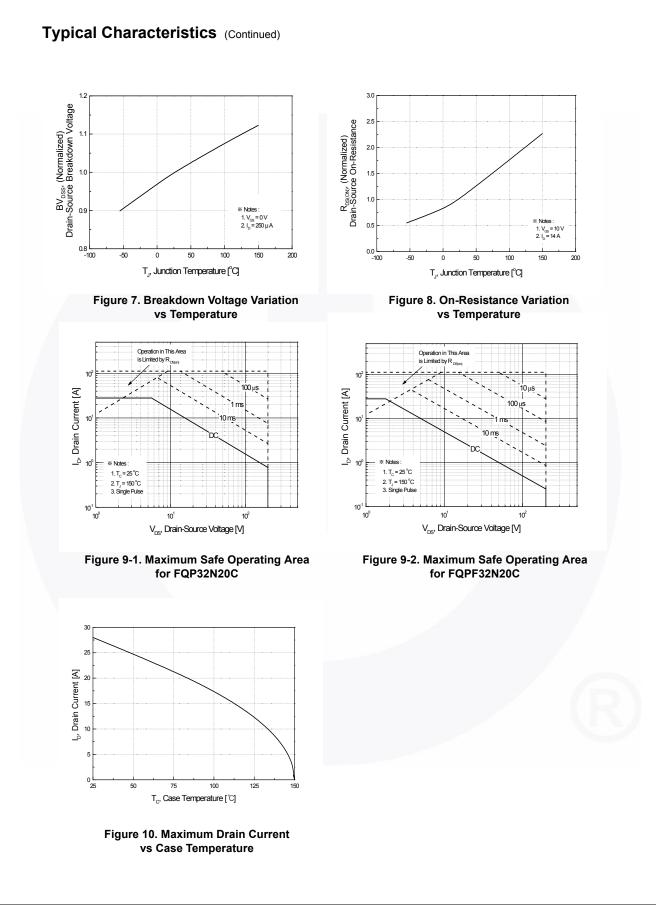
Device MarkingDeviceFQP32N20CFQP32N20CFQPF32N20CFQPF32N20C		Device	Package	Ree	l Size	Tape Width	n Qu	antity	
		FQP32N20C			ube	N/A	50	50 units	
		TO-220F Tu		ube	N/A	50 units			
lectri	cal Characte	eristics T _C = 25°C ur	nless otherwise noted.						
Symbol	Pa	arameter	Test Conditions	6	Min	Тур	Max	Unit	
Off Cha	racteristics								
BV _{DSS}	Drain-Source Bre	eakdown Voltage	V _{GS} = 0 V, I _D = 250 μA		200			V	
ΔBV _{DSS} / ΔT _J		ige Temperature Coeffi-	$I_D = 250 \mu$ A, Referenced to 25°C			0.24		V/°C	
		D 1 0 1	V _{DS} = 200 V, V _{GS} = 0 V				10	μA	
IDSS	Zero Gate Voltag	je Drain Current	$V_{DS} = 160 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$				100	μA	
I _{GSSF}	Gate-Body Leak	age Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V				100	nA	
I _{GSSR}	Gate-Body Leak	age Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V				-100	nA	
On Cha	racteristics								
V _{GS(th)}	Gate Threshold	Voltage	V_{DS} = V_{GS} , I_D = 250 μ A		2.0		4.0	V	
R _{DS(on)}	Static Drain-Sour On-Resistance	rce	V _{GS} = 10 V, I _D = 14 A			0.068	0.082	Ω	
9 _{FS}	Forward Transco	onductance	V _{DS} = 40 V, I _D = 14 A			20		S	
Dvnam	ic Characteris	tics							
C _{iss}	Input Capacitance		N 05 Y Y 0 Y			1700	2220	pF	
C _{oss}	Output Capacita		V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz			400	520	pF	
C _{rss}	Reverse Transfe					185	245	pF	
	1								
	ng Characteri								
t _{d(on)}	Turn-On Delay T		V_{DD} = 100 V, I _D = 32 A, R _G = 25 Ω			25	60	ns	
t _r	Turn-On Rise Tir					270	550	ns	
t _{d(off)}	Turn-Off Delay T					245	500	ns	
t _f	Turn-Off Fall Tim	e		(Note 4)		210	430	ns	
Qg	Total Gate Charg	je	V _{DS} = 160 V, I _D = 32 A,			82.5	110	nC	
Q _{gs}	Gate-Source Cha	•	V _{GS} = 10 V			10.5		nC	
Q _{gd}	Gate-Drain Char	ge		(Note 4)		44.5		nC	
Drain-S	ource Diode (Characteristics and	Maximum Ratings						
I _S	i	uous Drain-Source Diode					28	A	
I _{SM}	Maximum Pulsed	d Drain-Source Diode For	ward Current				112	Α	
V _{SD}		ode Forward Voltage	V _{GS} = 0 V, I _S = 28 A				1.5	V	
t _{rr}	Reverse Recove	•	V _{GS} = 0 V, I _S = 32 A,			265	-	ns	
Q _{rr}	Reverse Recove	,	dl _F / dt = 100 A/μs			2.73	-	μC	
otes:		, ,				-			

4. Essentially independent of operating temperature.

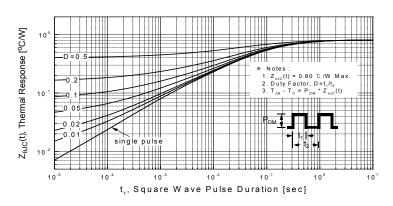
2



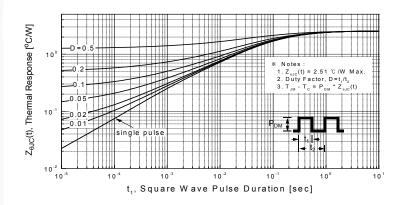
FQP32N20C / FQPF32N20C — N-Channel QFET[®] MOSFET



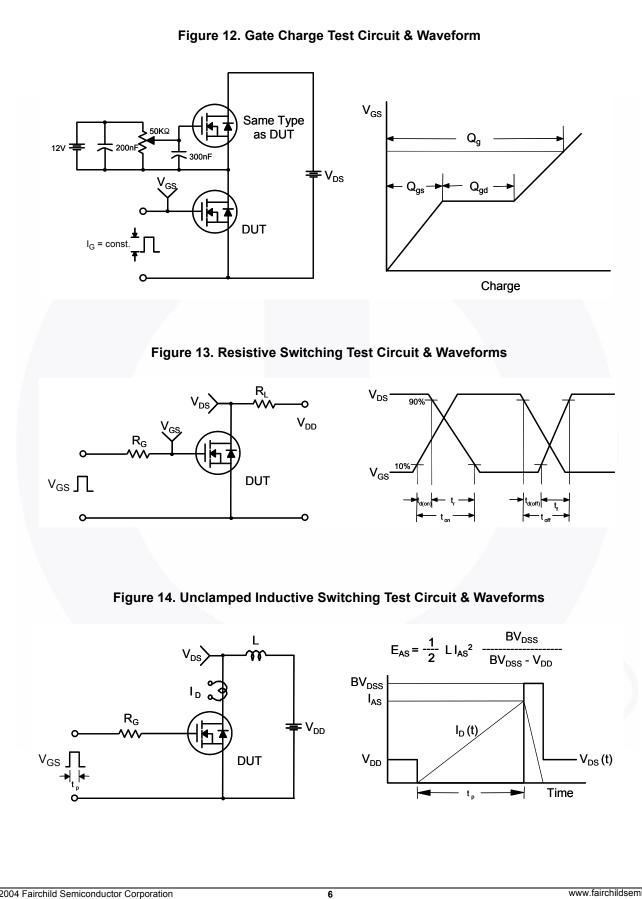
Typical Characteristics (Continued)



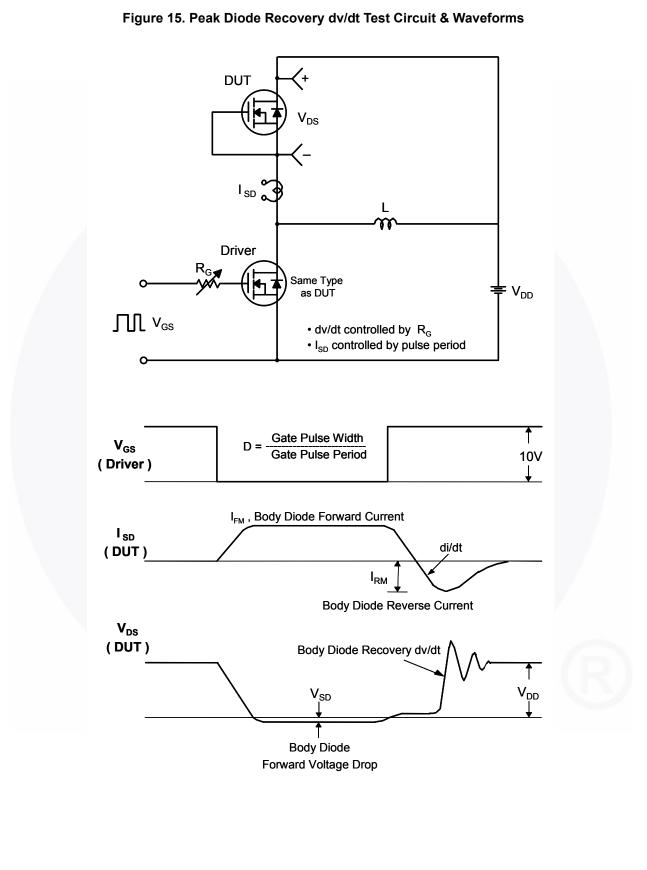




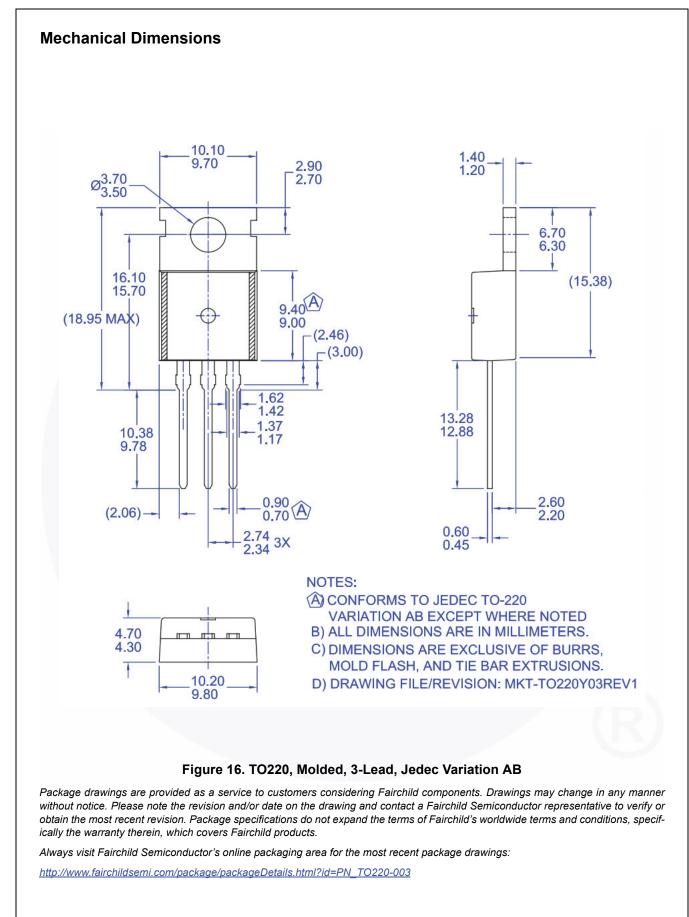


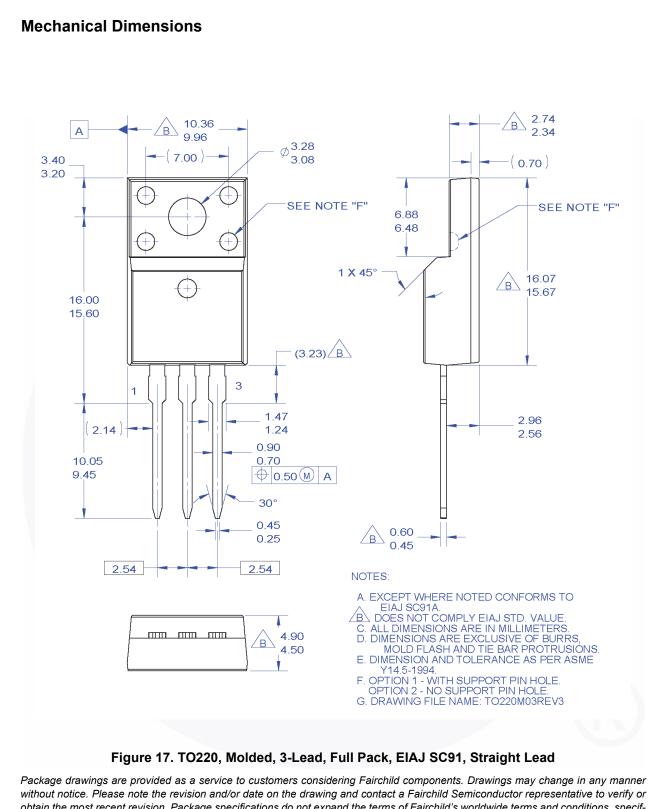


©2004 Fairchild Semiconductor Corporation FQP32N20C / FQPF32N20C Rev. C1



FQP32N20C / FQPF32N20C — N-Channel QFET® MOSFET





obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TF220-003

FQP32N20C / FQPF32N20C — N-Channel QFET[®] MOSFET



SEMICONDUCTOR

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™	F-PFS™	-215
AX-CAP [®] *	FRFET®	®
BitSiC™	Global Power Resource SM	PowerTrench [®]
Build it Now™	GreenBridge™	PowerXS™
CorePLUS™	Green FPS™	Programmable Active Droop™
CorePOWER™	Green FPS™ e-Series™	QFET®
CROSSVOLT™	Gmax™	QS™
CTL™	GTO™	Quiet Series™
Current Transfer Logic™	IntelliMAX™	RapidConfigure™
DEUXPEED®	ISOPLANAR™	[™]
Dual Cool™	Marking Small Speakers Sound Louder	
EcoSPARK [®]	and Better™	Saving our world, 1mW/W/kW at a time™
EfficentMax™	MegaBuck™	SignalWise™
ESBC™	MICROCOUPLER™	SmartMax™
r R	MicroFET™	SMART START™
+ °	MicroPak™	Solutions for Your Success™
Fairchild [®]	MicroPak2™	SPM®
Fairchild Semiconductor®	MillerDrive™	STEALTH™
FACT Quiet Series™	MotionMax™	SuperFET®
FACT®	mWSaver®	SuperSOT™-3
FAST®	OptoHiT™	SuperSOT™-6
FastvCore™	OPTOLOGIC®	SuperSOT™-8
FETBench™	OPTOPLANAR®	SupreMOS®
FPS™		SyncFET™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are 1. intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

Sync-Lock™ SYSTEM^{®*} GENERAL

TinyBoost TinyBuck® TinyCalc™ TinyLogic® TINYOPTO™

TinvPower™ TinyPWM™

TinyWire™

TranSiC™

UHC® Ultra FRFET™

VCX™

XS™

UniFFT™

VisualMax™

VoltagePlus™

TriFault Detect™

TRUECURRENT®* µSerDes™

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor haves against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly ori indirectly, any claim of personal injury or death

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Onsemi: FQPF32N20C FQP32N20C